

IRF630B/IRFS630B

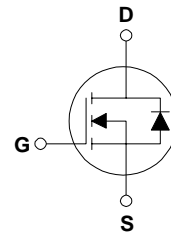
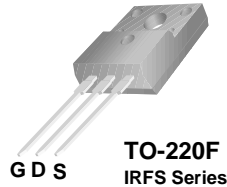
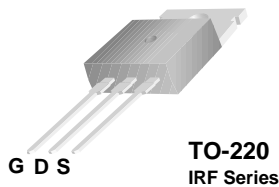
200V N-Channel MOSFET

General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supply and motor control.

Features

- 9.0A, 200V, $R_{DS(on)} = 0.4\Omega @ V_{GS} = 10V$
- Low gate charge (typical 22 nC)
- Low Crss (typical 22 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	IRF630B	IRFS630B	Units
V _{DSS}	Drain-Source Voltage	200		V
I _D	Drain Current - Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	9.0	9.0 *	A
		5.7	5.7 *	A
I _{DM}	Drain Current - Pulsed (Note 1)	36	36 *	A
V _{GSS}	Gate-Source Voltage	± 30		V
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	160		mJ
I _{AR}	Avalanche Current (Note 1)	9.0		A
E _{AR}	Repetitive Avalanche Energy (Note 1)	7.2		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	5.5		V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C	72	38	W
		0.57	0.3	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150		°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		°C

* Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	IRF630B	IRFS630B	Units
R _{θJC}	Thermal Resistance, Junction-to-Case Max.	1.74	3.33	°C/W
R _{θCS}	Thermal Resistance, Case-to-Sink Typ.	0.5	--	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient Max.	62.5	62.5	°C/W

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	200	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	--	0.2	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	μA
		$V_{DS} = 160\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$	--	0.34	0.4	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\text{ V}, I_D = 4.5\text{ A}$ (Note 4)	--	7.05	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	550	720	pF
C_{oss}	Output Capacitance		--	85	110	pF
C_{riss}	Reverse Transfer Capacitance		--	22	29	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 100\text{ V}, I_D = 9.0\text{ A},$ $R_G = 25\ \Omega$	--	11	30	ns
t_r	Turn-On Rise Time		--	70	150	ns
$t_{d(off)}$	Turn-Off Delay Time		--	60	130	ns
t_f	Turn-Off Fall Time		(Note 4, 5)	--	65	140
Q_g	Total Gate Charge	$V_{DS} = 160\text{ V}, I_D = 9.0\text{ A},$ $V_{GS} = 10\text{ V}$	--	22	29	nC
Q_{gs}	Gate-Source Charge		--	3.6	--	nC
Q_{gd}	Gate-Drain Charge		(Note 4, 5)	--	10.2	--

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	9.0	A	
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	36	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 9.0\text{ A}$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 9.0\text{ A},$	--	140	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	0.87	--	μC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 3\text{ mH}, I_{AS} = 9.0\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 9.0\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

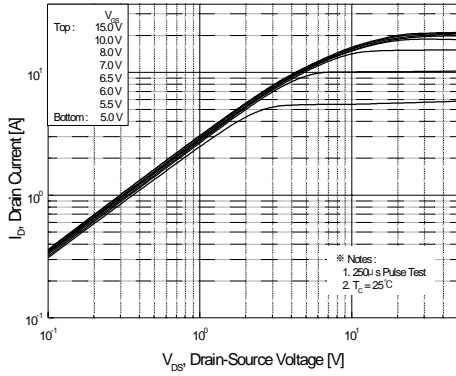


Figure 1. On-Region Characteristics

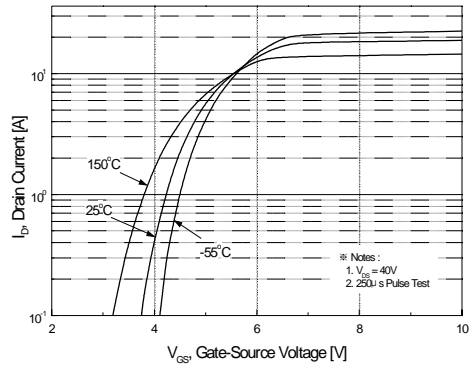


Figure 2. Transfer Characteristics

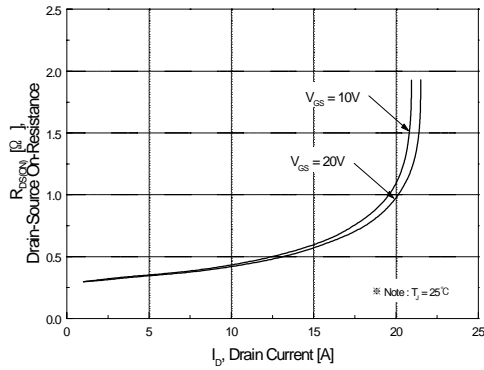


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

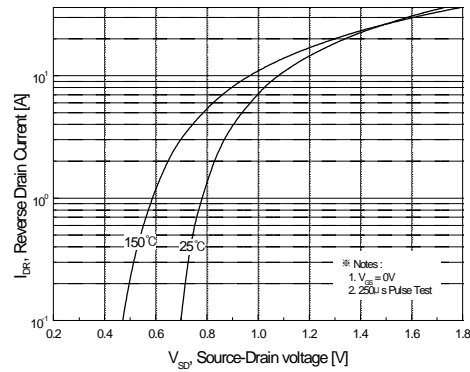


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

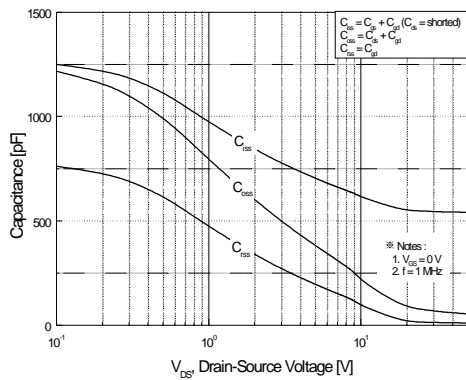


Figure 5. Capacitance Characteristics

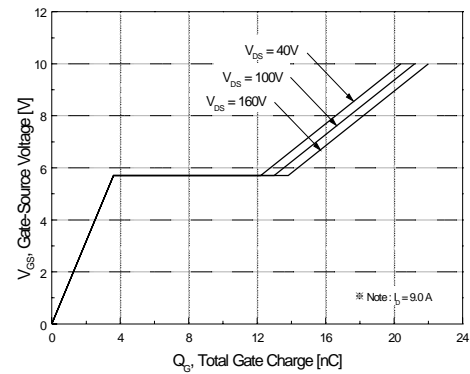


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

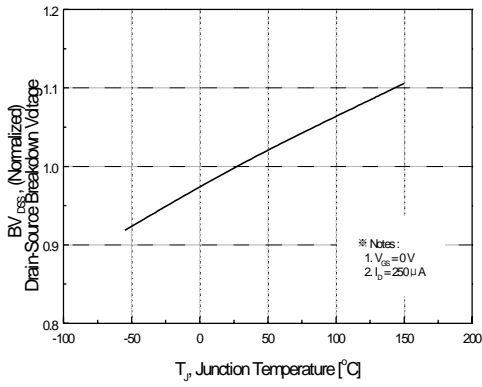


Figure 7. Breakdown Voltage Variation vs Temperature

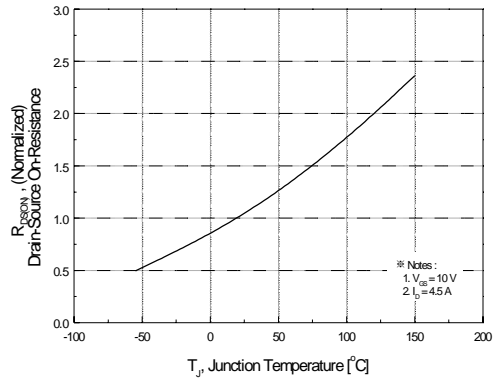


Figure 8. On-Resistance Variation vs Temperature

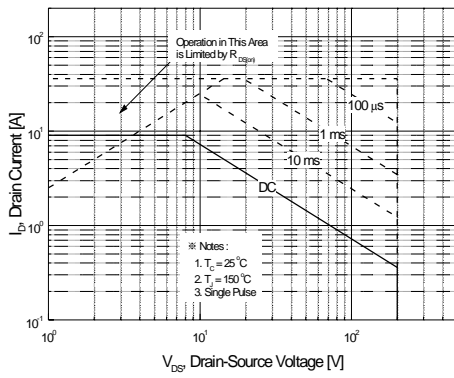


Figure 9-1. Maximum Safe Operating Area for IRF630B

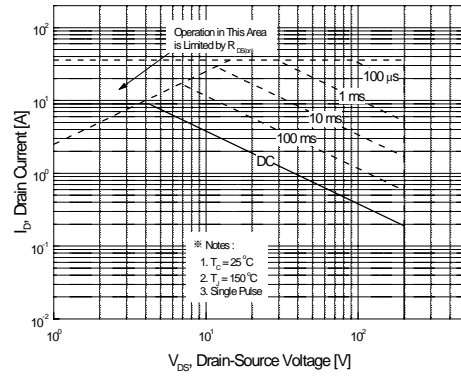


Figure 9-2. Maximum Safe Operating Area for IRFS630B

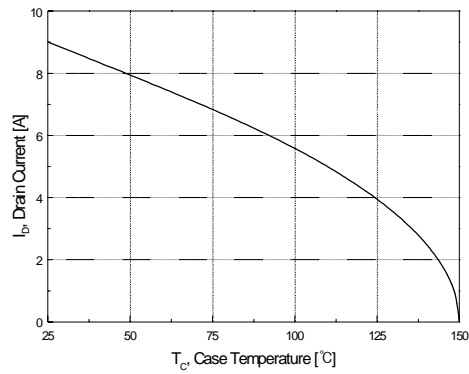


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

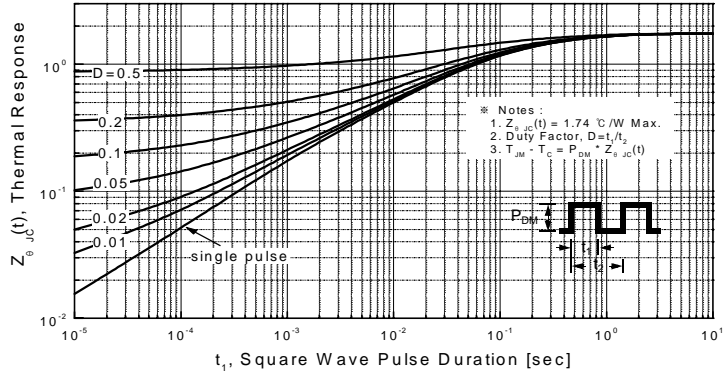


Figure 11-1. Transient Thermal Response Curve for IRF630B

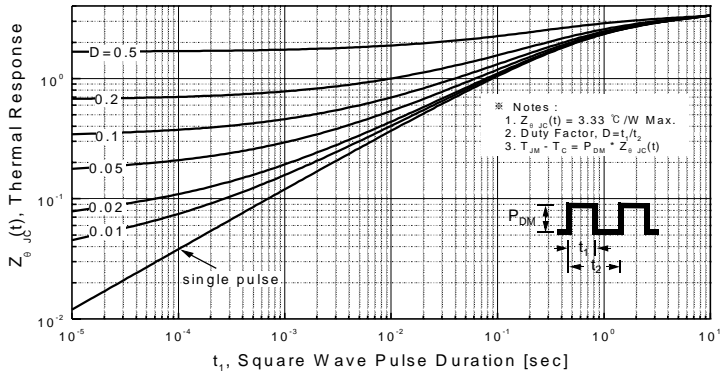


Figure 11-2. Transient Thermal Response Curve for IRFS630B

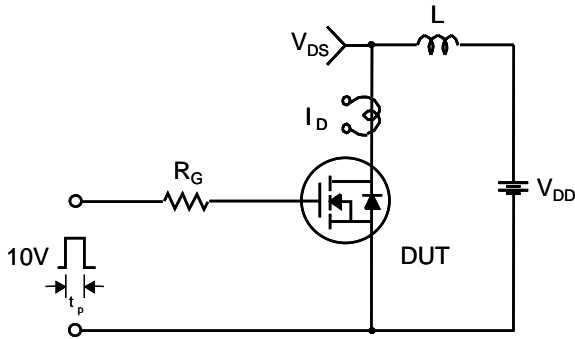
Gate Charge Test Circuit & Waveform



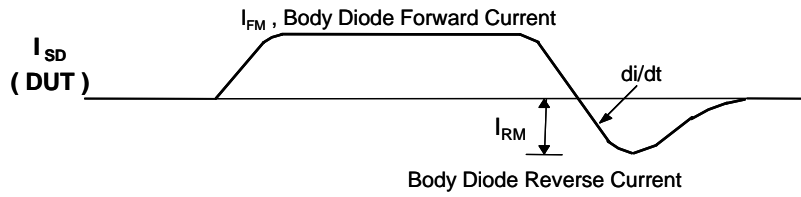
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

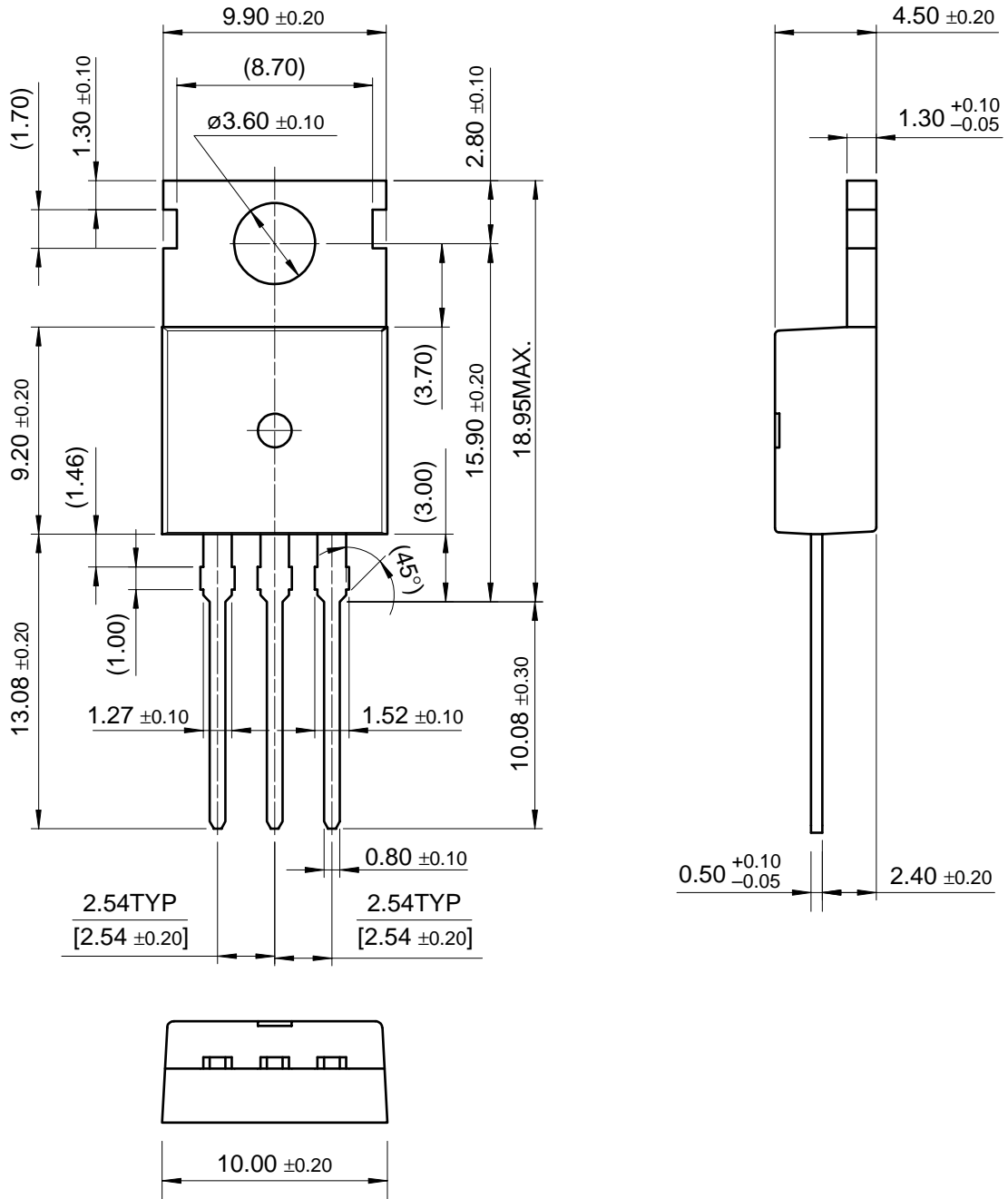


Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

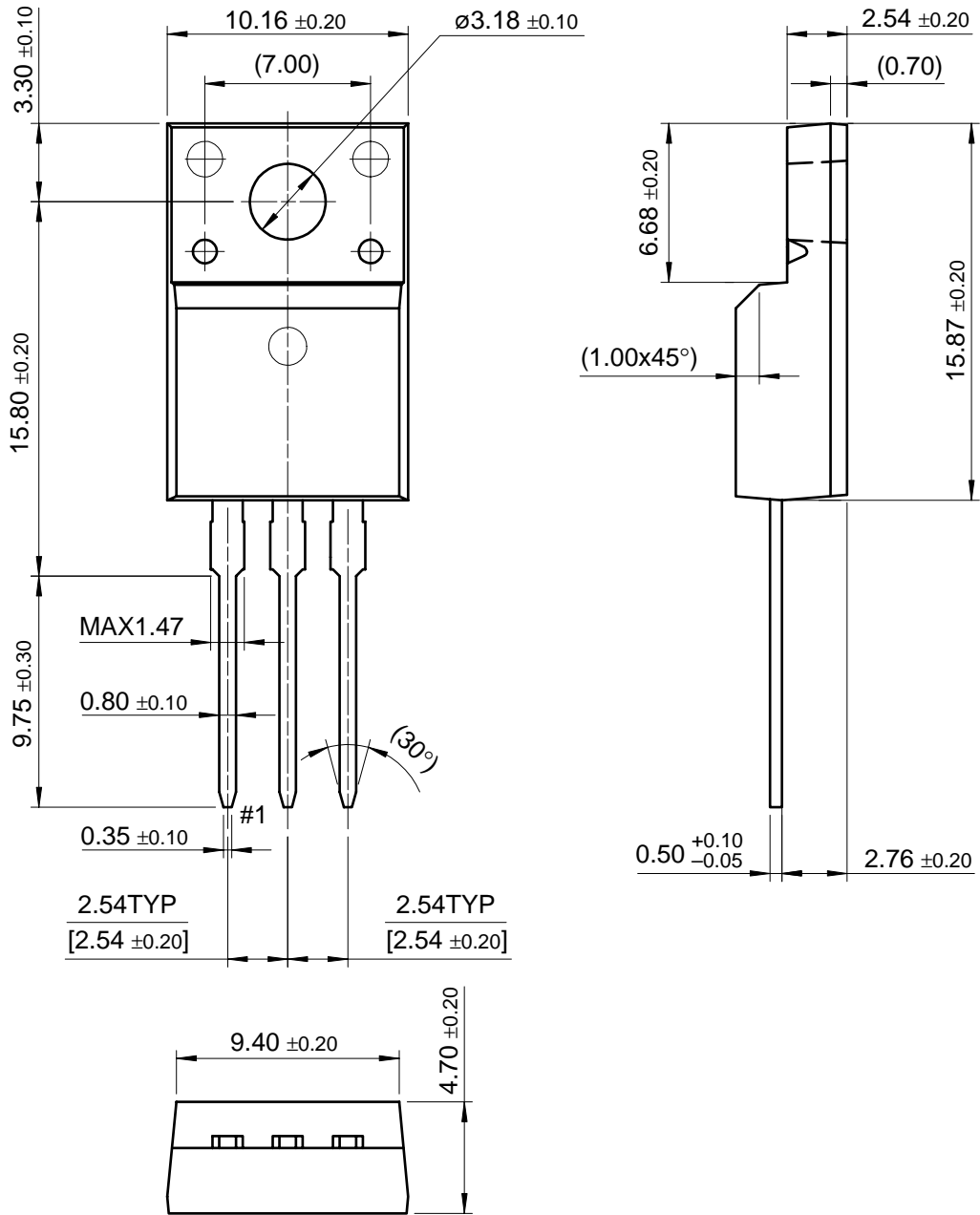
TO-220



Dimensions in Millimeters

Package Dimensions (Continued)

TO-220F



IRF630B/IRFS630B

Dimensions in Millimeters

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Definition of Terms

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

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IRF630B

200V N-Channel B-FET / Substitute of IRF630 & IRF630A

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General description

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Product status/pricing/packaging

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Product	Product status	Pb-free Status	Package type	Leads	Packing method	Package Marking Convention**
IRF630BTSTU_FP001	Not recommended for new designs		TO-220	3	RAIL	Line 1: \$Y (Fairchild logo) & Z (Asm. Plant Code) & 4 (4-Digit Date Code) Line 2: IRF Line 3: 630B
IRF630B_FP001	Not recommended for new designs		TO-220	3	RAIL	Line 1: \$Y (Fairchild logo) & Z (Asm. Plant Code) & 4 (4-Digit Date Code) Line 2: IRF Line 3: 630B



Indicates product with Pb-free second-level interconnect. For more information [click here](#).

Package marking information for product IRF630B is available. [Click here for more information](#).

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Qualification Support

Click on a product for detailed qualification data

Product
IRF630BTSTU_FP001
IRF630B_FP001

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